

Description

The SX40P04NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -40V$ $I_D = -40 A$

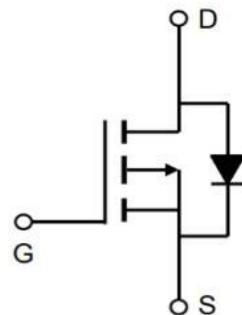
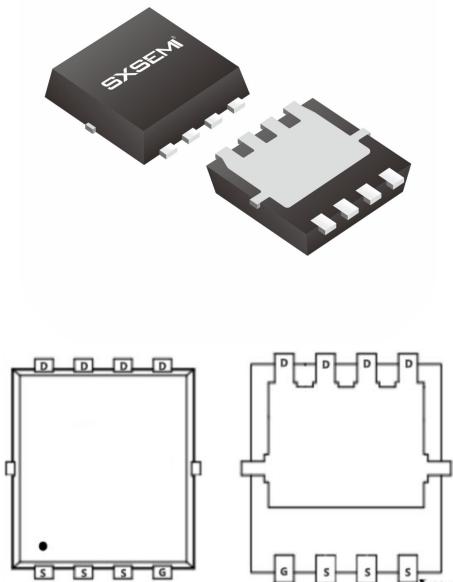
$R_{DS(ON)} < 18m\Omega$ @ $V_{GS} = -10V$

Application

Battery protection

Load switch

Uninterruptible power supply

PDFN5*6-8L**Absolute Maximum Ratings (TC=25°C unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-40	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-23	A
I_{DM}	Pulsed Drain Current ²	-120	A
EAS	Single Pulse Avalanche Energy ³	125	mJ
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	25	W
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ⁴	16	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	25	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	5	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}$, $\text{I}_D=-250\mu\text{A}$	-40	-44	---	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $\text{I}_D=-1\text{mA}$	---	-0.023	---	$\text{V}/^\circ\text{C}$
$\text{R}_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$\text{V}_{\text{GS}}=-10\text{V}$, $\text{I}_D=-30\text{A}$	---	15	18	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-4.5\text{V}$, $\text{I}_D=-20\text{A}$	---	18	25	
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{GS}}=\text{V}_{\text{DS}}$, $\text{I}_D=-250\mu\text{A}$	-1.0	-1.6	-2.5	V
$\Delta \text{V}_{\text{GS(th)}}$	$\text{V}_{\text{GS(th)}}$ Temperature Coefficient		---	4.74	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$\text{V}_{\text{DS}}=-40\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $\text{T}_J=25^\circ\text{C}$	---	---	1	uA
		$\text{V}_{\text{DS}}=-40\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $\text{T}_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$\text{V}_{\text{GS}}=\pm 20\text{V}$, $\text{V}_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Q_g	Total Gate Charge (-4.5V)	$\text{V}_{\text{DS}}=-20\text{V}$, $\text{V}_{\text{GS}}=-4.5\text{V}$, $\text{I}_D=-12\text{A}$	---	25	---	nC
Q_{gs}	Gate-Source Charge		---	11	---	
Q_{gd}	Gate-Drain Charge		---	9.5	---	
$\text{T}_{\text{d(on)}}$	Turn-On Delay Time	$\text{VDD} = -15\text{V}$, $\text{RL}=15\Omega$ $\text{ID} = -1\text{A}$, $\text{VGEN} = -10\text{V}$, $\text{RG} = 6\Omega$	---	48	---	ns
T_r	Rise Time		---	24	---	
$\text{T}_{\text{d(off)}}$	Turn-Off Delay Time		---	88	---	
T_f	Fall Time		---	9.6	---	
C_{iss}	Input Capacitance	$\text{V}_{\text{DS}}=-20\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	2760	---	pF
C_{oss}	Output Capacitance		---	260	---	
C_{rss}	Reverse Transfer Capacitance		---	85	---	
I_{s}	Continuous Source Current ^{1,5}	$\text{V}_G=\text{V}_D=0\text{V}$, Force Current	---	---	-40	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-90	A
V_{SD}	Diode Forward Voltage ²	$\text{V}_{\text{GS}}=0\text{V}$, $\text{I}_S=-1\text{A}$, $\text{T}_J=25^\circ\text{C}$	---	---	-1.3	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $\text{VDD}=-32\text{V}$, $\text{VGS}=-10\text{V}$, $\text{L}=0.1\text{mH}$, $\text{IAS}=-30\text{A}$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

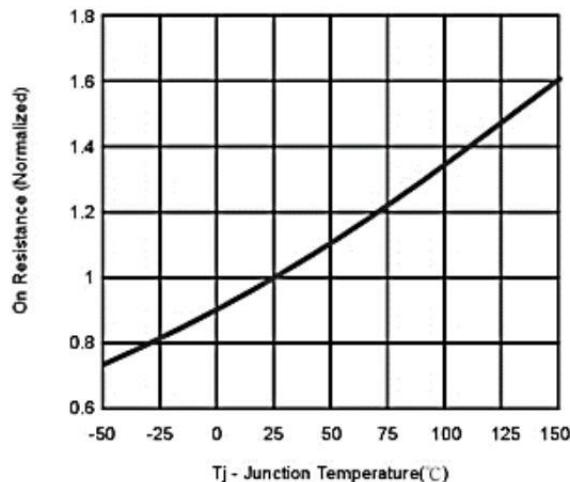


Fig. 1 On Resistance Vs Junction Temperature

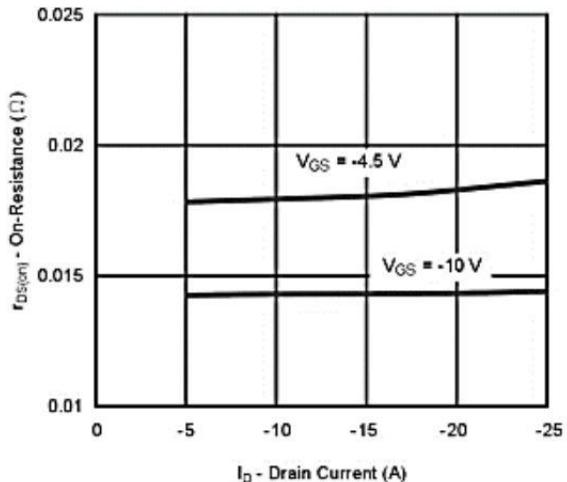


Fig.2 On-Resistance Vs.Drain Current

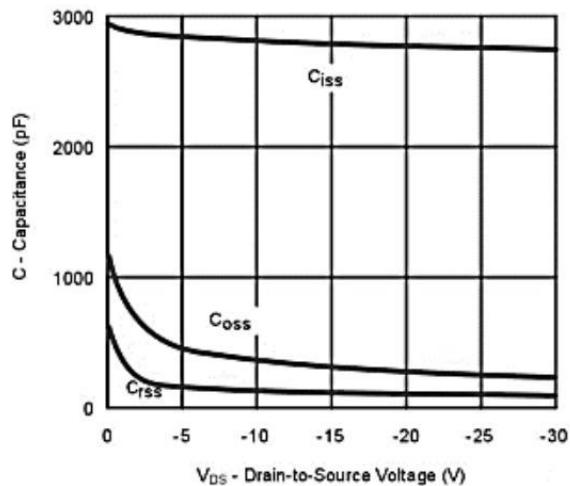


Fig.3 Capacitance

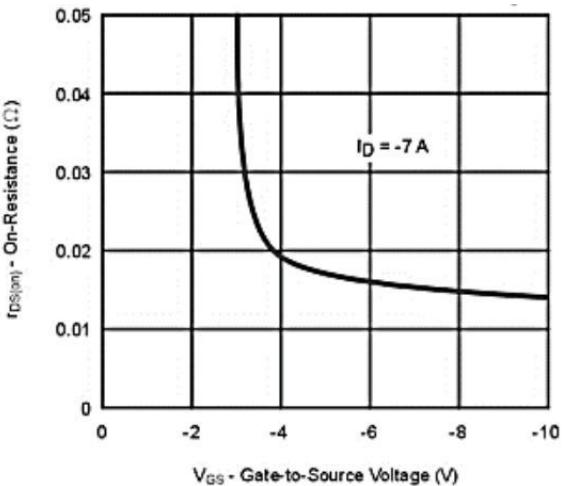


Fig.4 On-Resistance Vs. Gate-to-Sourece Voltage

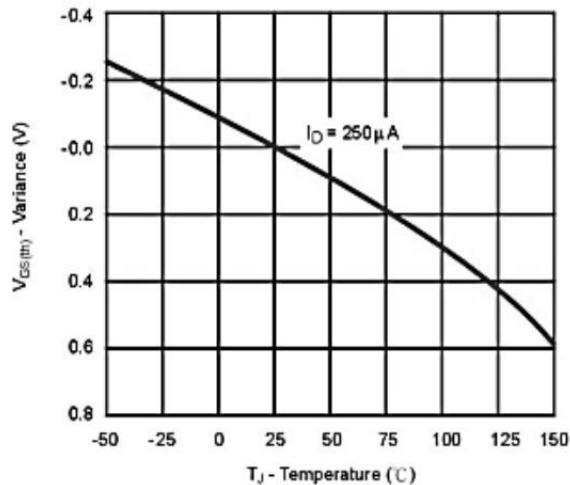


Fig.5 Threshold Voltage

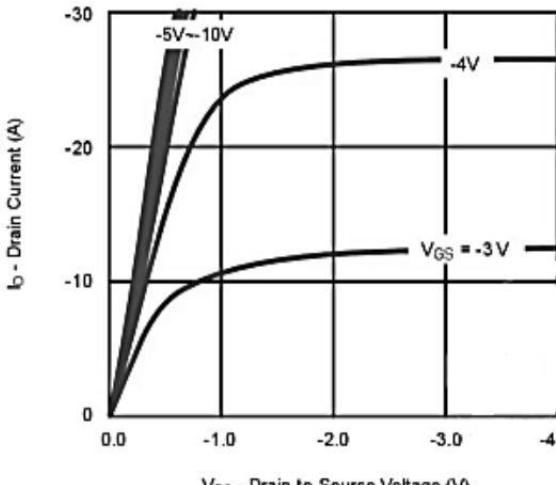


Fig.6 On-Region Characteristics

Typical Characteristics

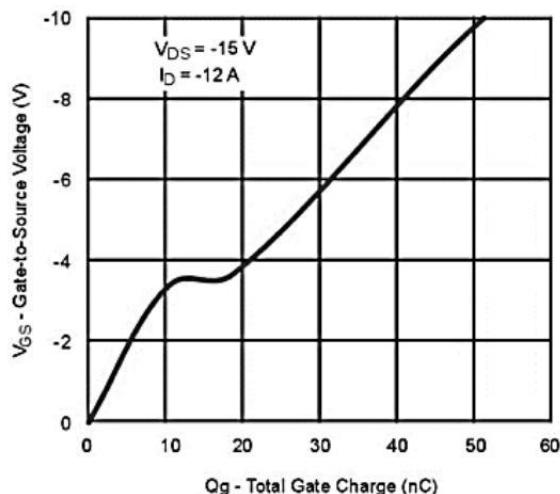


Fig.7 Gate Charge

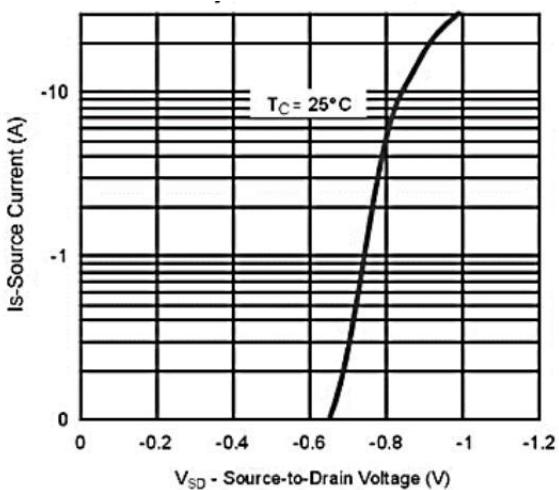


Fig.8 Body-diode Characteristic

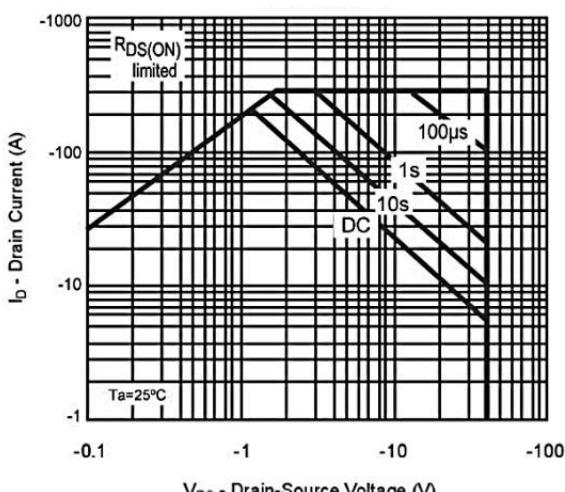


Fig.9 Safe Operating Area

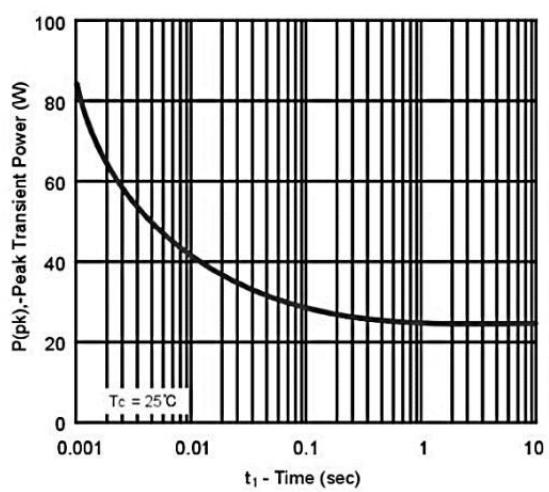


Fig.10 Single Pulse Maximum Power Dissipation

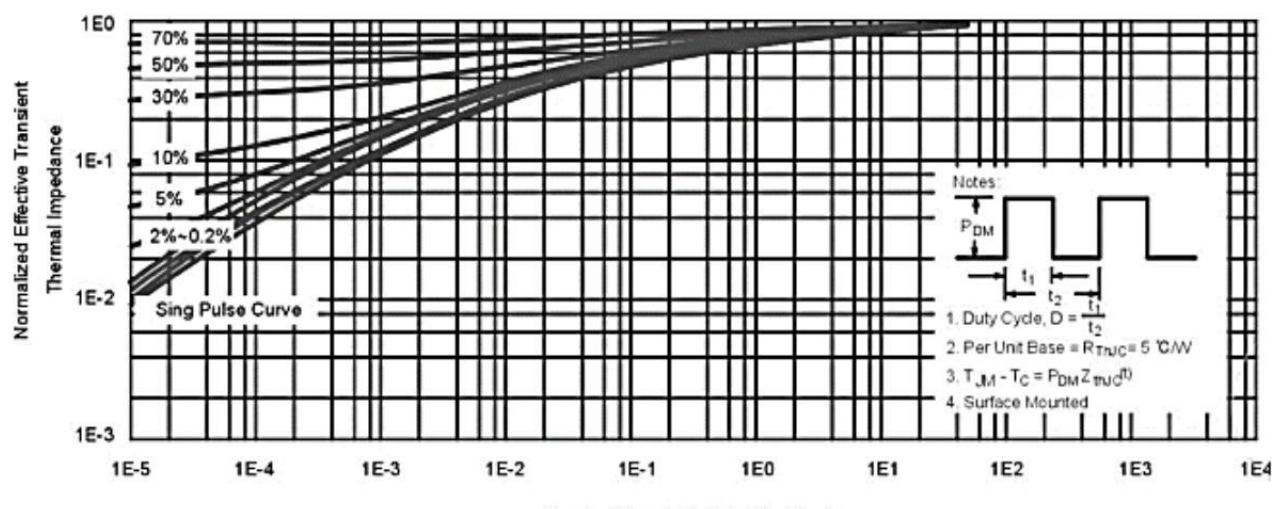
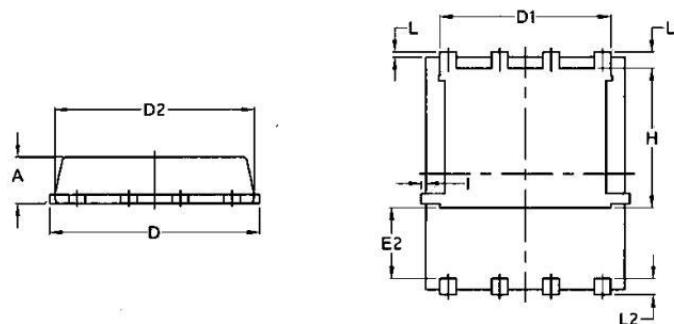
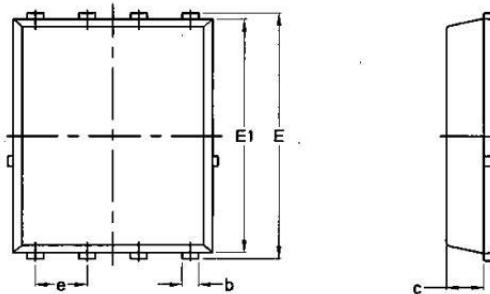


Fig.11 Normalized Maximum Transient Thermal Impedance

Package Mechanical Data-PDFN5*6-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5*6-8L		5000